

FEAST - [resistor.wsp.1]

File View Edit Tools Window Help

Design Explorer

Active

- L1: (31807) (bitline\$1 or (bit adj line\$1)) a
- L2: (11175) 1 and dielectric
- L3: (3876) 2 and (ROM or (read adj2 memory))
- L4: (2380) 3 and (etch\$3)
- L5: (1695) 4 and (etch\$3 near7 (dielectric or
- L6: (1875) 4 and (etch\$3 near7 (dielectric or
- L7: (713) 6 and (bitline\$1.clm. or (bit adj 1
- L8: (200) 7 and (etch\$3 near7 (dielectric or
- L9: (200) 8 and etch\$3.clm.
- L10: (100) 9 and (3D or (three adj dimensions
- L11: (37) 9 and (ROM.clm. or (read adj memory
- L12: (0) 7 and neck\$1

ADON: 199904010001

Date: 9/20/99

9 and (ROM.clm. or (read adj memory).clm.)

System: 4 64K ROM 128K RAM 16 MB

	U	I	PT	S	Document ID	Issue Date	Pages	Title	Current OR	Current XB	Retrieval	Inventor	S	C	I	A
1					US 20040113191	20040617	13	Memory circuitry and method of forming memor	257/296	257/E21.64		Coursey, Belford T.				
2					US 20040071030	20040415	69	Semiconductor integrated circuits, fa	365/222	9		Goda, Akira et al.				
3					US 200404008	20040408	10	UV-programmed P-type mask ROM and fabricatio	257/390	257/208, 257/391		Kuo, Tung-Cheng et al.				
4					US 20030232284	20031218	18	Method of forming a system on chip	430/314	257/E21.61		Liu, Chien-Hung et al.				
5					US 20030183882	20031002	10	UV-programmed P-type Mask ROM and fabricatio	257/390	257/E21.67		Kuo, Tung-Cheng et al.				
6					US 20030724	20030724	13	Dynamic random access memory circuitry	438/241	257/E21.64		Coursey, Belford T.				
7					US 20030139007	20030710	11	Method of making identification code of	365/200	257/E21.67		Wen, Wen-Ying et al.				
8					US 20030612	20030612	11	Method of making identification code of	438/401	257/390, 257/391		Wen, Wen-Ying et al.				
9					US 20030109113	20030123	13	Dynamic random access memory circuitry	257/296	257/306, 257/309		Coursey, Belford T.				
10					US 20030015745	20030123	13	Method of forming memory circuitry	257/296	257/306, 257/E21.64		Coursey, Belford T.				
11					US 20030015744	20030102	21	Apparatus and methods for monitoring self-all	438/16			Weiner, Kurt H. et al.				
12					US 20030003611	20020509	11	Non-volatile memory device used for non-ove	257/390	257/391, 257/E21.67		Chang, Ching-Yu				
13					US 20020053708	20020228	13	Methods of forming dynamic random access m	438/128	257/E21.64		Coursey, Belford T.				
14					US 20020025609	20020228	13	Memory Circuitry and Dynamic Random Access M	257/306	257/E21.64		Coursey, Belford T.				
15					US 20020024084	20010913	28	ROM-embedded-DRAM	365/149	257/E21.64		Kurth, Casey R. et al.				
16					US 20010021122	20010809	27	Multi-level dram trench store utilizing two can	365/149	257/E21.08		Furukawa, Toshiharu et al.				
17					US 6699757	20040302	14	Method for manufacturing embedded	438/262	257/E21.67		Hwang, Chong Jen				